Abstracts

A 1.57 W/mm GaAs-Based MISFET for High-Power and Microwave-Switching Applications

F.W. Smith, C.L. Chen, L.J. Mahoney, M.J. Manfra, D.H. Temme, B.J. Clifton and A.R. Calawa. "A 1.57 W/mm GaAs-Based MISFET for High-Power and Microwave-Switching Applications." 1991 MTT-S International Microwave Symposium Digest 91.2 (1991 Vol. II [MWSYM]): 643-646.

A GaAs-based MISFET delivered a record output power density of 1.57 W/mm at 1.1 GHz. An RF switch based upon this device has a figure of merit (R/sub on/C/sub off/) better than that of the best commercial MESFET we have tested.

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